Ordering number:EN3462A

N-Channel Silicon MOSFET

2SK1459

Ultrahigh-Speed Switching Applications

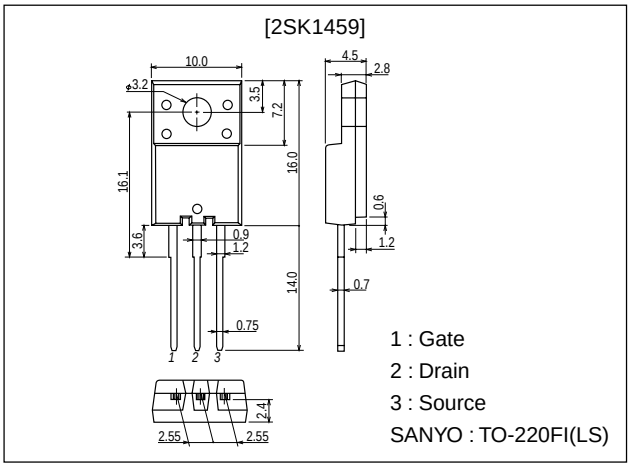
Features

- Low ON-state resistance.
- Ultrahigh-speed switching.
- Micaless package facilitating mounting.

Package Dimensions

unit:mm

2078B



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		900	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_D		2.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	5	A
Allowable Power Dissipation	P_D		2.0	W
		Tc=25°C	30	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	900			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V, V_{GS}=0			1.0	mA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0			±100	nA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	2.0		3.0	V
Forward Transfer Admittance	| yfs |	V_{DS}=20V, I_D=1.5A	0.8	1.5		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=1.5A, V_{GS}=10V		4.7	6.0	Ω

(Note) Be careful in handling the 2SK1459 because it has no protection diode between gate and source.

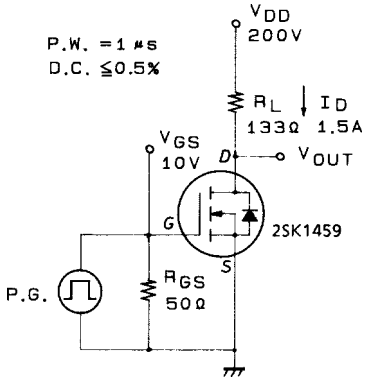
Continued on next page.

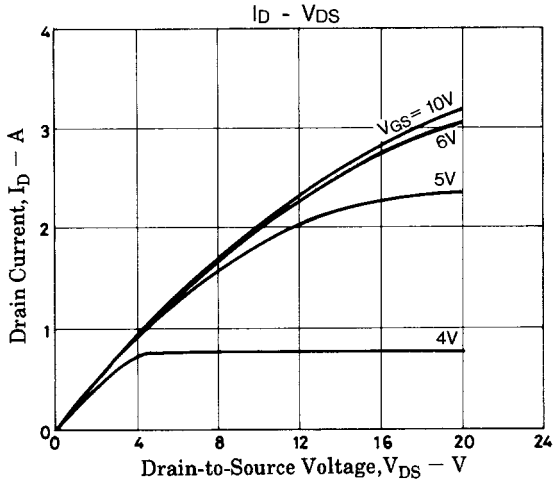
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

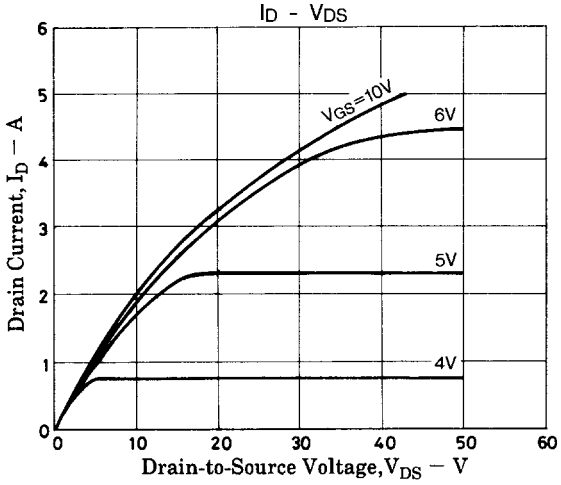
Continued from preceding page.

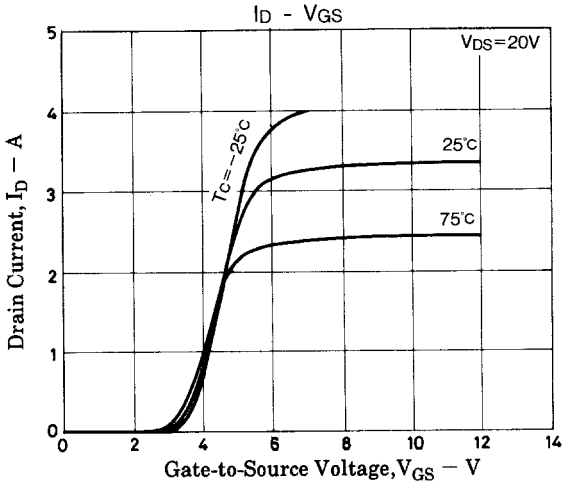
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		350		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		150		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		100		pF
Turn-ON Delay Time	$t_{d(on)}$	I_D=1.5A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		15		ns
Rise Time	t_r	I_D=1.5A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		25		ns
Turn-OFF Delay Time	$t_{d(off)}$	I_D=1.5A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		120		ns
Fall Time	t_f	I_D=1.5A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		40		ns
Diode Forward Voltage	V_{SD}	I_S=2.5A, V_{GS}=0			1.8	V

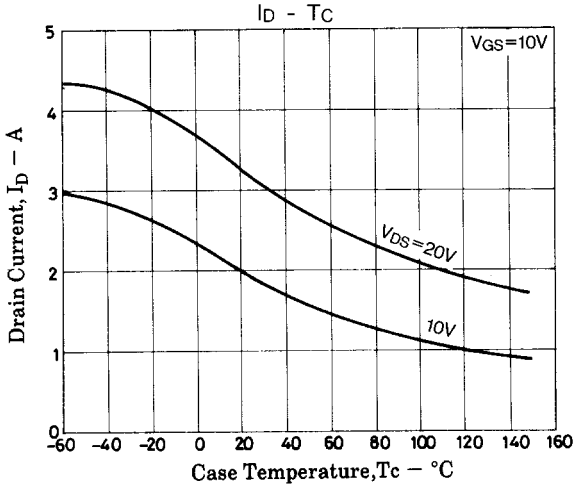
Switching Time Test Circuit

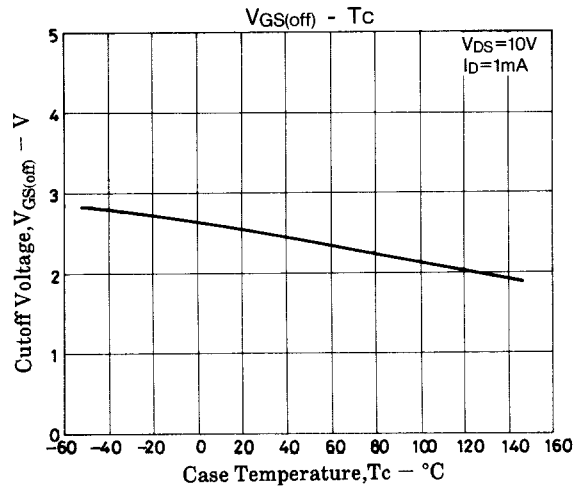


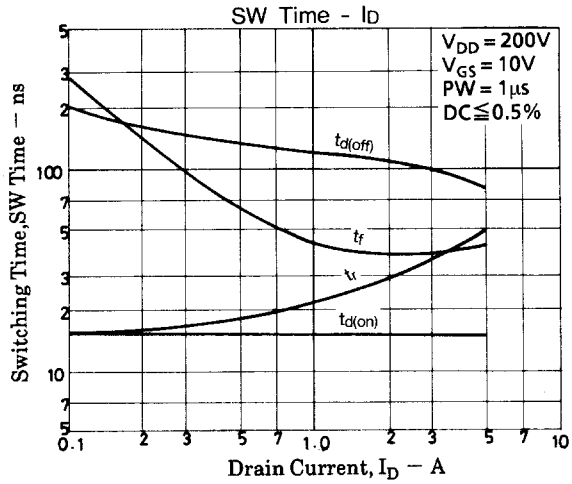


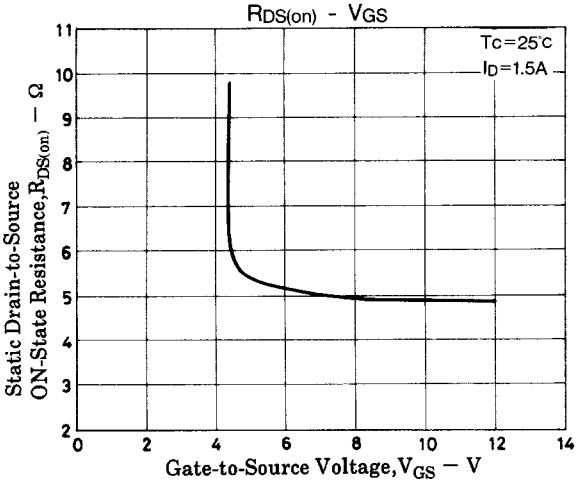


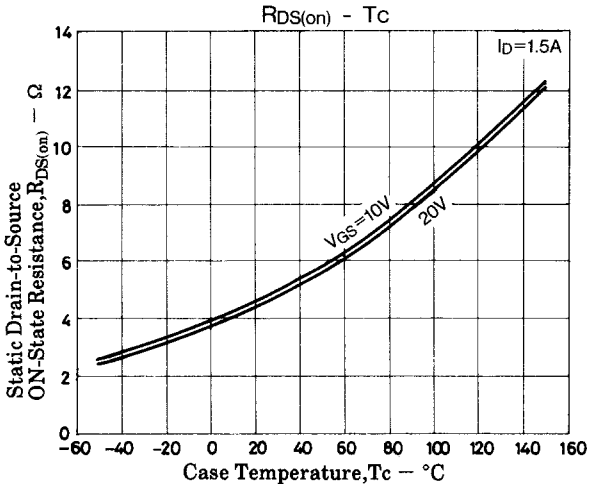


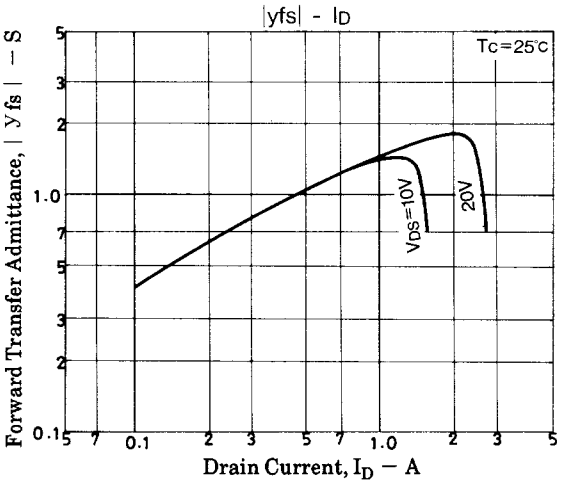


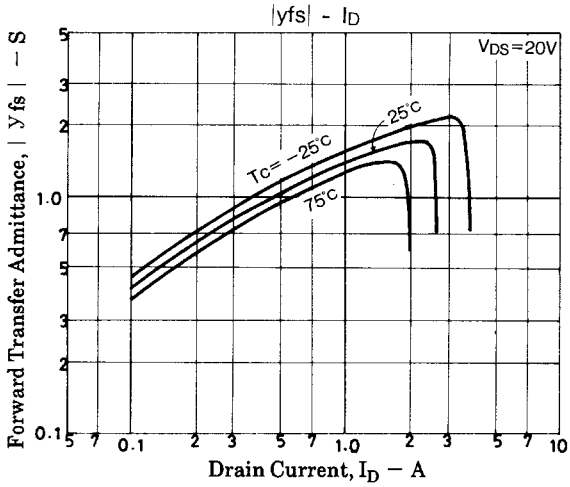

VGS(off) - Tc
VDS=10V
ID=1mA
Cutoff Voltage, VGS(off) — V
Case Temperature, Tc — °C

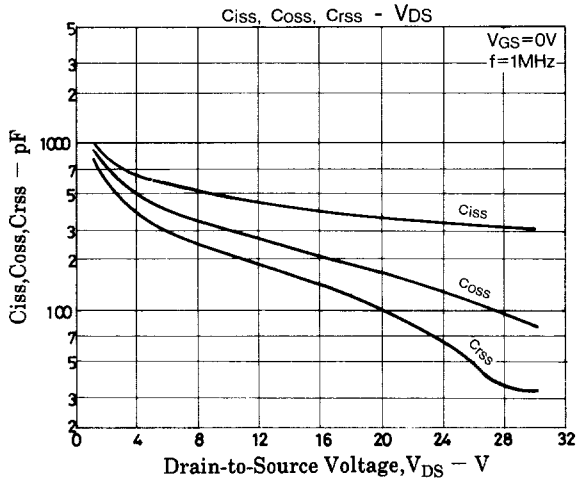

SW Time - ID
VDD=200V
VGS=10V
PW=1μs
DC≦0.5%
td(off)
tf
tr
td(on)
Switching Time, SW Time — ns
Drain Current, ID — A

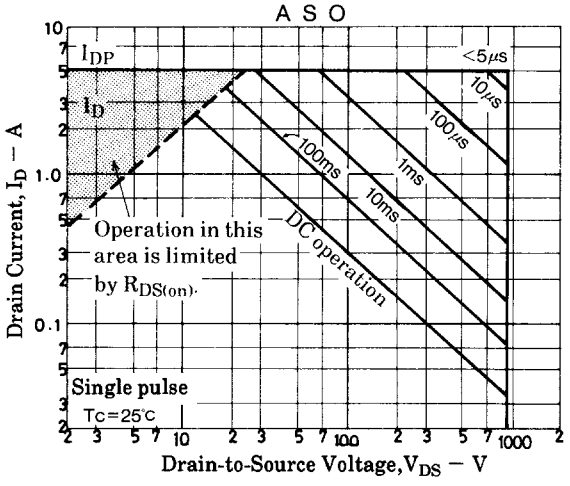

RDS(on) - VGS
Tc=25°C
ID=1.5A
Static Drain-to-Source ON-State Resistance, RDS(on) — Ω
Gate-to-Source Voltage, VGS — V


RDS(on) - Tc
ID=1.5A
VGS=10V
20V
Static Drain-to-Source ON-State Resistance, RDS(on) — Ω
Case Temperature, Tc — °C


|yfs| - ID
Tc=25°C
VDS=10V
20V
Forward Transfer Admittance, | yfs | — S
Drain Current, ID — A


|yfs| - ID
VDS=20V
Tc=−25°C
25°C
75°C
Forward Transfer Admittance, | yfs | — S
Drain Current, ID — A


Ciss, Coss, Crss - VDS
VGS=0V
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss — pF
Drain-to-Source Voltage, VDS — V


A S O
IDP
ID
<5μs
10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Single pulse
Tc=25°C
Drain Current, ID — A
Drain-to-Source Voltage, VDS — V